

NTJD4401N, NVJD4401N

Small Signal MOSFET

20 V, Dual N-Channel, SC-88

ESD Protection

Features

- Small Footprint (2 x 2 mm)
- Low Gate Charge N-Channel Device
- ESD Protected Gate
- Same Package as SC-70 (6 Leads)
- AEC-Q101 Qualified and PPAP Capable – NVJD4401N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Load Power Switching
- Li-Ion Battery Supplied Devices
- Cell Phones, Media Players, Digital Cameras, PDAs
- DC-DC Conversion

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current (Based on $R_{\theta JA}$)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	0.63	A
		$T_A = 85^{\circ}\text{C}$		0.46	
Power Dissipation (Based on $R_{\theta JA}$)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	0.27	W
		$T_A = 85^{\circ}\text{C}$		0.14	
Continuous Drain Current (Based on $R_{\theta JL}$)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	0.91	A
		$T_A = 85^{\circ}\text{C}$		0.65	
Power Dissipation (Based on $R_{\theta JL}$)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	0.55	W
		$T_A = 85^{\circ}\text{C}$		0.29	
Pulsed Drain Current		$t \leq 10 \mu\text{s}$	I_{DM}	± 1.2	A
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Continuous Source Current (Body Diode)			I_S	0.63	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Typ	Max	Units
Junction-to-Ambient – Steady State	$R_{\theta JA}$	400	458	$^\circ\text{C/W}$
Junction-to-Lead (Drain) – Steady State	$R_{\theta JL}$	194	252	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 oz Cu area = 0.9523 in sq.

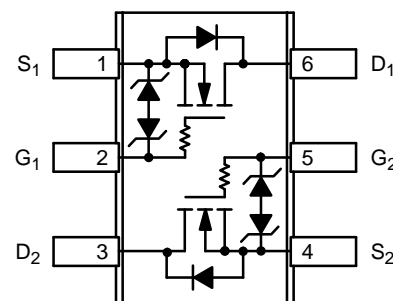


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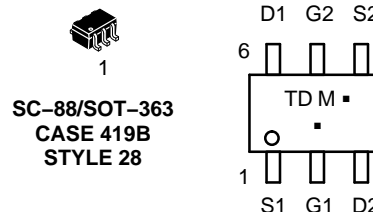
$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
20 V	0.29 Ω @ 4.5 V	0.63 A
	0.36 Ω @ 2.5 V	

SC-88 (SOT-363)



Top View

MARKING DIAGRAM & PIN ASSIGNMENT



TD = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NTJD4401N, NVJD4401N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20	27		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			22		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 16 V			1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.6	0.92	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-2.1		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 0.63 A		0.29	0.375	Ω
		V _{GS} = 2.5 V, I _D = 0.40 A		0.36	0.445	
Forward Transconductance	g _{FS}	V _{DS} = 4.0 V, I _D = 0.63 A		2.0		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 20 V		33	46	pF
Output Capacitance	C _{OSS}			13	22	
Reverse Transfer Capacitance	C _{RSS}			2.8	5.0	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		1.3	3.0	nC
Threshold Gate Charge	Q _{G(TH)}			0.1		
Gate-to-Source Charge	Q _{GS}			0.2		
Gate-to-Drain Charge	Q _{GD}			0.4		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 0.5 A, R _G = 20 Ω		0.083		μs
Rise Time	t _r			0.227		
Turn-Off Delay Time	t _{d(OFF)}			0.786		
Fall Time	t _f			0.506		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 0.23 A	T _J = 25°C		0.76	1.1	V
			T _J = 125°C		0.63		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 0.63 A			0.410		μs

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

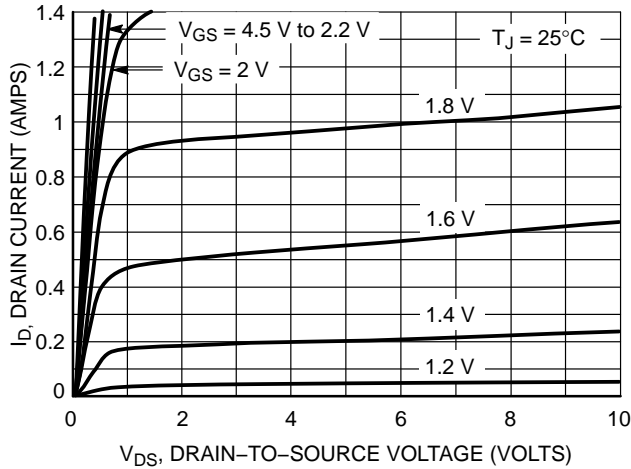


Figure 1. On-Region Characteristics

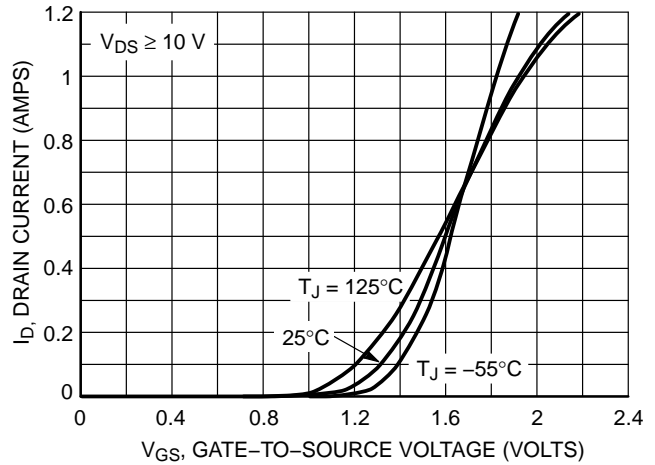


Figure 2. Transfer Characteristics

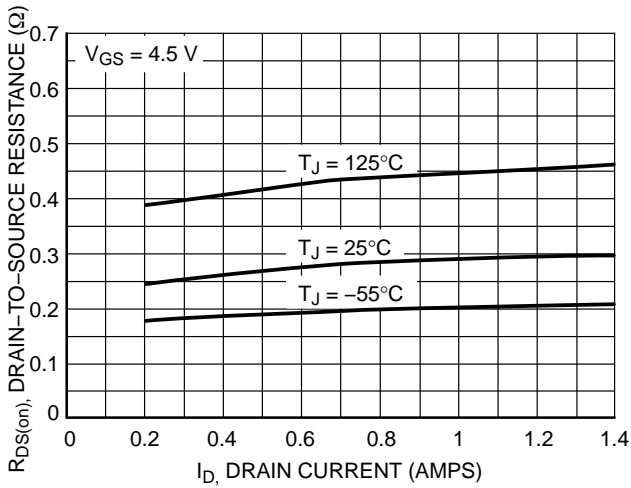


Figure 3. On-Resistance vs. Drain Current and Temperature

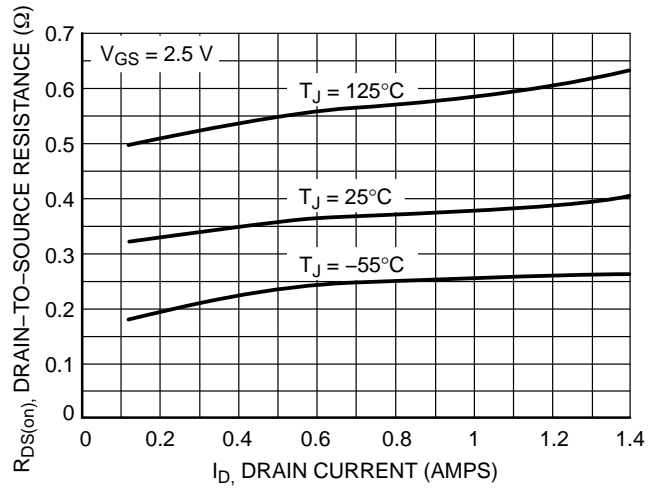


Figure 4. On-Resistance vs. Drain Current and Temperature

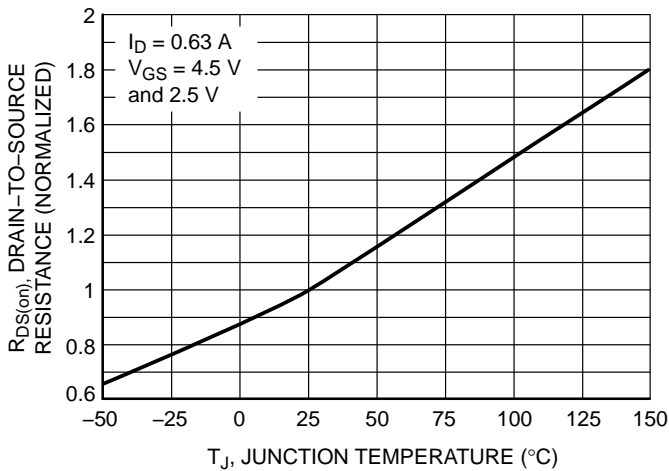


Figure 5. On-Resistance Variation with Temperature

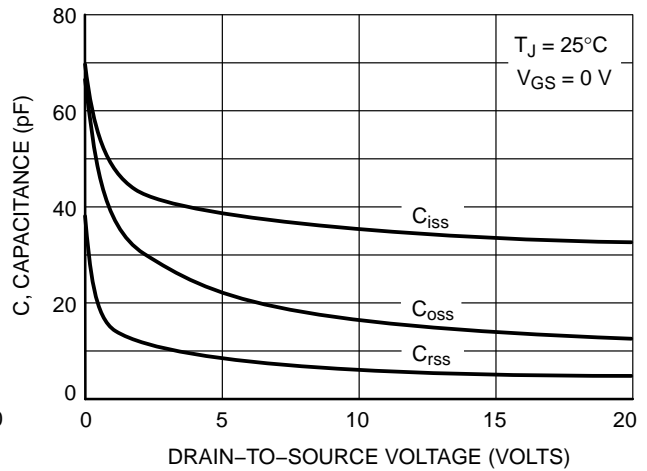


Figure 6. Capacitance Variation

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

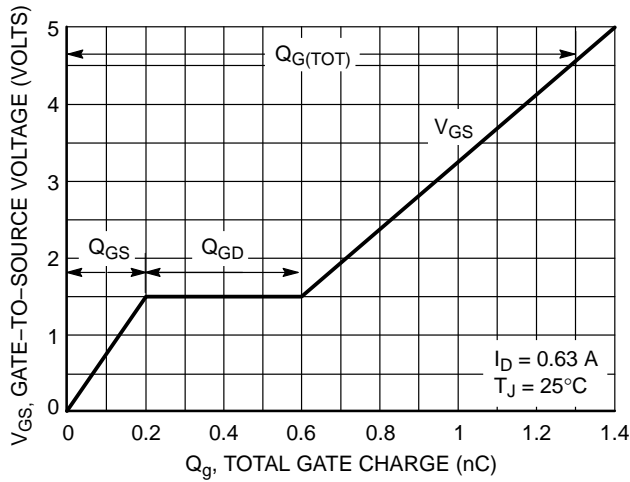


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

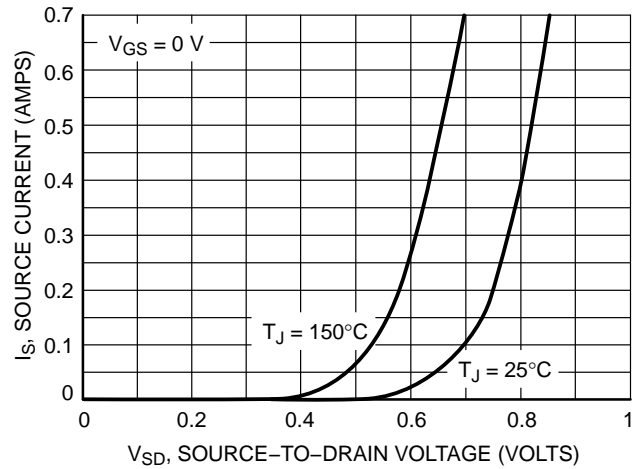


Figure 8. Diode Forward Voltage vs. Current

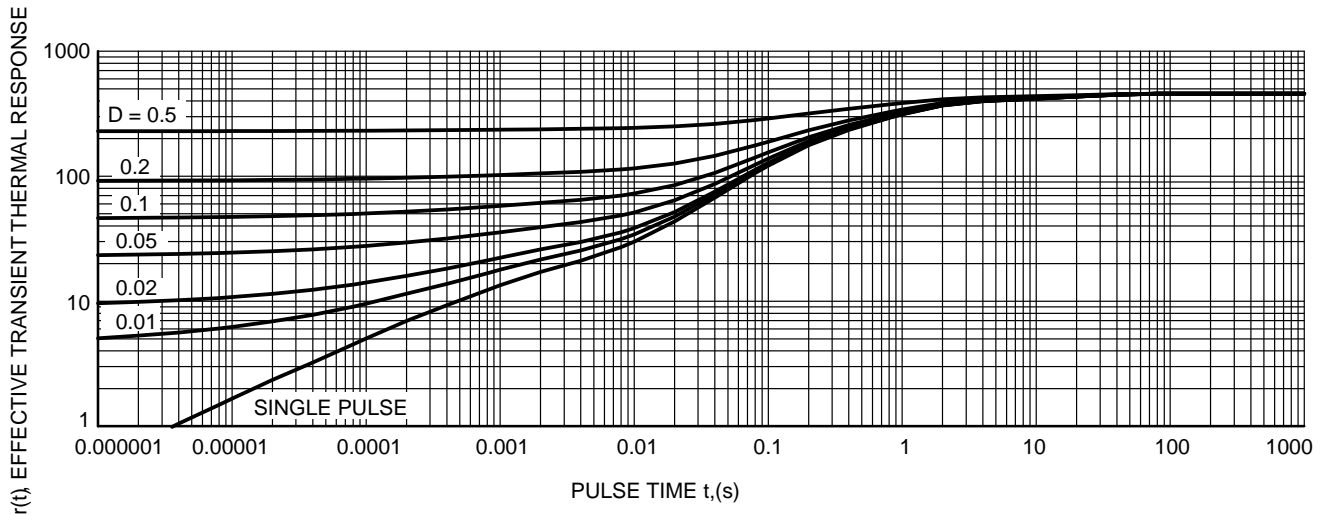


Figure 9. Thermal Response

ORDERING INFORMATION

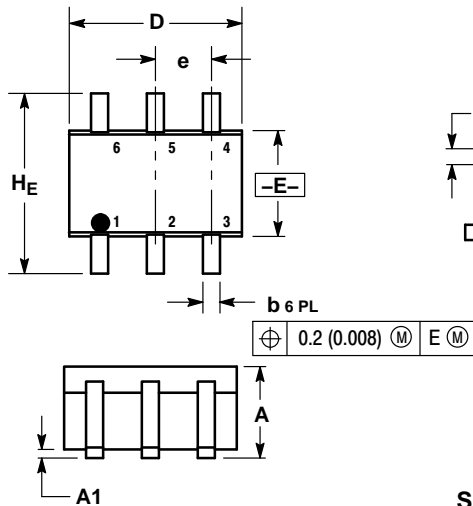
Device	Package	Shipping [†]
NTJD4401NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD4401NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTJD4401N, NVJD4401N

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W



NOTES:

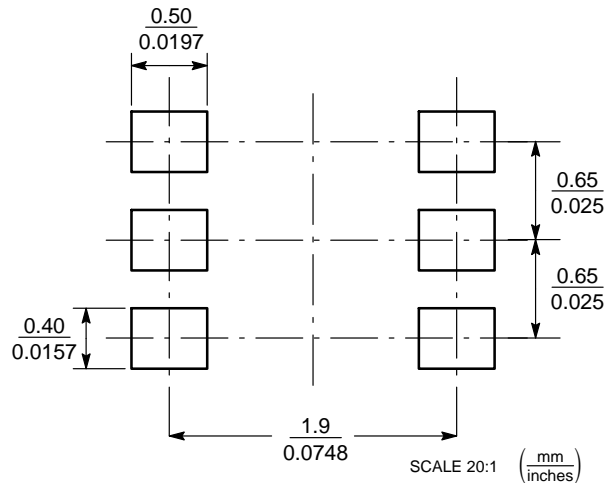
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 26:

- PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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